

Features

- Freq: 6~18GHz
- Isolation: 20dB
- Insertion Loss: 0.8dB
- Chip Size: 1.55mm×1.25mm×0.1mm

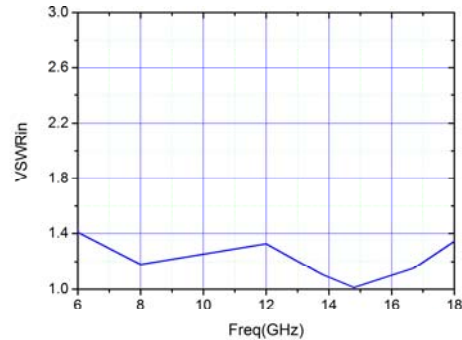
General Description

The HG126GA is a 2-way GaAs pHEMT power divider that is operating from 6 to 18 GHz. This chip features very high isolation of 20dB and extremely low insertion loss of 0.8dB. Input and output VSWR are 1.3/1.3.

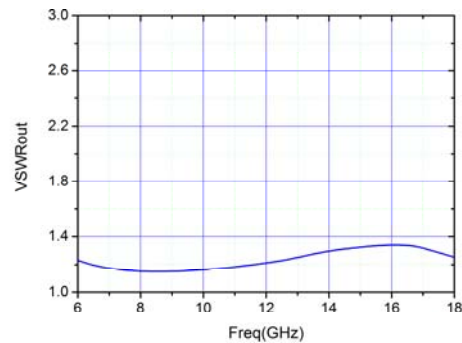
Electrical Specifications ($T_A=25^\circ\text{C}$)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	6~18		
Input VSWR	-	1.3	-
Output VSWR	-	1.3	-
Insertion Loss(dB)	-	0.8	-
Isolation (dB)	-	20	-

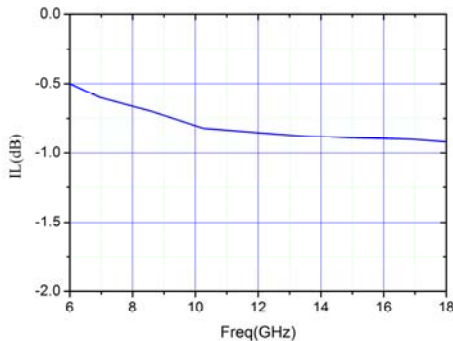
Input VSWR



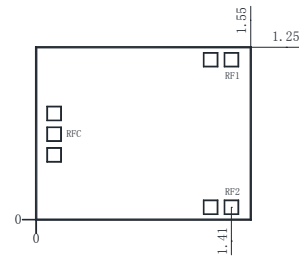
Output VSWR



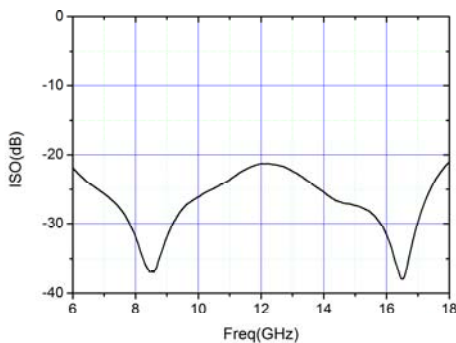
Insertion Loss



Outline Drawing (mm)



Isolation



Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

Notes:

- The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
- GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
- The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
- The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
- Chip microwave port without DC blocking capacitor.
- The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.